

PHASE CONTROL THYRISTORS

Hockey Puk Version

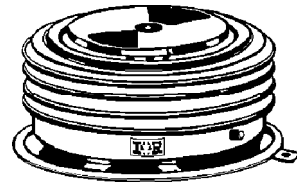
Features

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case A-24 (K-PUK)
- High profile hockey-puk

Typical Applications

- DC motor controls
- Controlled DC power supplies
- AC controllers

1745A



case style A-24 (K-PUK)

Major Ratings and Characteristics

Parameters	ST1230C..K	Units
$I_{T(AV)}$	1745	A
	@ T_{hs}	55 °C
$I_{T(RMS)}$	3200	A
	@ T_{hs}	25 °C
I_{TSM}	@ 50Hz	33500 A
	@ 60Hz	35100 A
I^2t	@ 50Hz	5615 KA ² s
	@ 60Hz	5126 KA ² s
V_{DRM}/V_{RRM}	800 to 1600	V
t_q typical	200	μs
T_J	- 40 to 125	°C

ELECTRICAL SPECIFICATIONS

Voltage Ratings

Type number	Voltage Code	V_{DRM}/V_{RRM} , max. repetitive peak and off-state voltage V	V_{RSM} , maximum non-repetitive peak voltage V	I_{DRM}/I_{RRM} max. @ $T_J = T_J$ max mA
ST1230C..K	08	800	900	100
	12	1200	1300	
	14	1400	1500	
	16	1600	1700	

On-state Conduction

Parameter	ST1230C..K	Units	Conditions	
$I_{T(AV)}$ Max. average on-state current @ Heatsink temperature	1745 (710)	A	180° conduction, half sine wave double side (single side) cooled	
	55 (85)	°C		
$I_{T(RMS)}$ Max. RMS on-state current	3200	A	DC @ 25°C heatsink temperature double side cooled	
I_{TSM} Max. peak, one-cycle non-repetitive surge current	33500		t = 10ms	No voltage
	35100		t = 8.3ms	reapplied
	28200		t = 10ms	100% V_{RRM}
	29500	t = 8.3ms	reapplied	
I^2t Maximum I^2t for fusing	5615	KA ² s	t = 10ms	Sinusoidal half wave, Initial $T_J = T_J$ max.
	5126		t = 8.3ms	
	3971		t = 10ms	
	3625		t = 8.3ms	
$I^2\sqrt{t}$ Maximum $I^2\sqrt{t}$ for fusing	56150	KA ² √s	t = 0.1 to 10ms, no voltage reapplied	
$V_{T(TO)1}$ Low level value of threshold voltage	0.93	V	(16.7% x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ max.	
$V_{T(TO)2}$ High level value of threshold voltage	1.02		($I > \pi$ x $I_{T(AV)}$), $T_J = T_J$ max.	
r_{t1} Low level value of on-state slope resistance	0.17	mΩ	(16.7% x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ max.	
r_{t2} High level value of on-state slope resistance	0.16		($I > \pi$ x $I_{T(AV)}$), $T_J = T_J$ max.	
V_{TM} Max. on-state voltage	1.62	V	$I_{pk} = 4000A$, $T_J = T_J$ max, $t_p = 10ms$ sine pulse	
I_H Maximum holding current	600	mA	$T_J = 25^\circ C$, anode supply 12V resistive load	
I_L Typical latching current	1000			

Switching

Parameter	ST1230C..K	Units	Conditions
di/dt Max. non-repetitive rate of rise of turned-on current	1000	A/ μ s	Gate drive 20V, 20 Ω , $t_r \leq 1\mu$ s $T_J = T_J$ max, anode voltage $\leq 80\%$ V_{DRM}
t_d Typical delay time	1.9	μ s	Gate current 1A, $di_g/dt = 1A/\mu$ s $V_d = 0.67\%$ V_{DRM} , $T_J = 25^\circ$ C
t_q Typical turn-off time	200		$I_{TM} = 550A$, $T_J = T_J$ max, $di/dt = 40A/\mu$ s, $V_R = 50V$ $dv/dt = 20V/\mu$ s, Gate 0V 100 Ω , $t_p = 500\mu$ s

Blocking

Parameter	ST1230C..K	Units	Conditions
dv/dt Maximum critical rate of rise of off-state voltage	500	V/ μ s	$T_J = T_J$ max. linear to 80% rated V_{DRM}
I_{RRM} I_{DRM} Max. peak reverse and off-state leakage current	100	mA	$T_J = T_J$ max, rated V_{DRM}/V_{RRM} applied

Triggering

Parameter	ST1230C..K	Units	Conditions		
P_{GM} Maximum peak gate power	16	W	$T_J = T_J$ max, $t_p \leq 5$ ms		
$P_{G(AV)}$ Maximum average gate power	3		$T_J = T_J$ max, $f = 50$ Hz, $d\% = 50$		
I_{GM} Max. peak positive gate current	3.0	A	$T_J = T_J$ max, $t_p \leq 5$ ms		
$+V_{GM}$ Maximum peak positive gate voltage	20	V	$T_J = T_J$ max, $t_p \leq 5$ ms		
$-V_{GM}$ Maximum peak negative gate voltage	5.0				
I_{GT} DC gate current required to trigger	TYP.	MAX.	mA	$T_J = -40^\circ$ C $T_J = 25^\circ$ C $T_J = 125^\circ$ C	Max. required gate trigger/ current/ voltage are the lowest value which will trigger all units 12V anode-to-cathode applied
	200	-			
	100	200			
V_{GT} DC gate voltage required to trigger	1.4	-	V	$T_J = -40^\circ$ C $T_J = 25^\circ$ C $T_J = 125^\circ$ C	
	1.1	3.0			
	0.9	-			
I_{GD} DC gate current not to trigger	10	mA	$T_J = T_J$ max	Max. gate current/voltage not to trigger is the max. value which will not trigger any unit with rated V_{DRM} anode-to-cathode applied	
V_{GD} DC gate voltage not to trigger	0.25	V			

ST1230C..K Series

Thermal and Mechanical Specification

Parameter	ST1230C..K	Units	Conditions
T _J Max. operating temperature range	-40 to 125	°C	
T _{stg} Max. storage temperature range	-40 to 150		
R _{thJ-hs} Max. thermal resistance, junction to heatsink	0.042 0.021	K/W	DC operation single side cooled DC operation double side cooled
R _{thC-hs} Max. thermal resistance, case to heatsink	0.006 0.003	K/W	DC operation single side cooled DC operation double side cooled
F Mounting force, ± 10%	24500 (2500)	N (Kg)	
wt Approximate weight	425	g	
Case style	A-24 (K-PUK)		See Outline Table

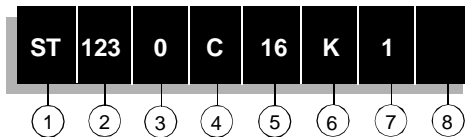
ΔR_{thJ-hs} Conduction

(The following table shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC)

Conduction angle	Sinusoidal conduction		Rectangular conduction		Units	Conditions
	Single Side	Double Side	Single Side	Double Side		
180°	0.003	0.003	0.002	0.002	K/W	T _J = T _J max.
120°	0.004	0.004	0.004	0.004		
90°	0.005	0.005	0.005	0.005		
60°	0.007	0.007	0.007	0.007		
30°	0.012	0.012	0.012	0.012		

Ordering Information Table

Device Code



- 1** - Thyristor
- 2** - Essential part number
- 3** - 0 = Converter grade
- 4** - C = Ceramic Puk
- 5** - Voltage code: Code x 100 = V_{RRM} (See Voltage Rating Table)
- 6** - K = Puk Case A-24 (K-PUK)
- 7** - 0 = Eyelet terminals (Gate and Auxiliary Cathode Unsoldered Leads)
1 = Fast-on terminals (Gate and Auxiliary Cathode Unsoldered Leads)
2 = Eyelet terminals (Gate and Auxiliary Cathode Soldered Leads)
3 = Fast-on terminals (Gate and Auxiliary Cathode Soldered Leads)
- 8** - Critical dv/dt: None = 500V/μsec (Standard selection)
L = 1000V/μsec (Special selection)

Outline Table

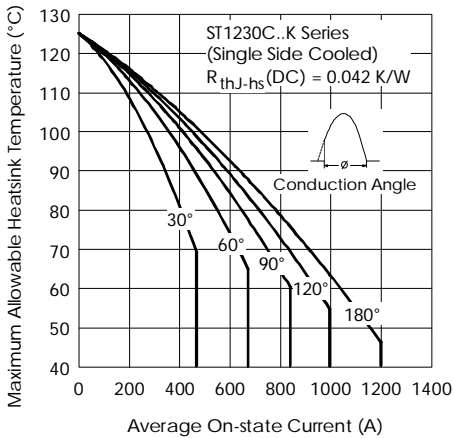
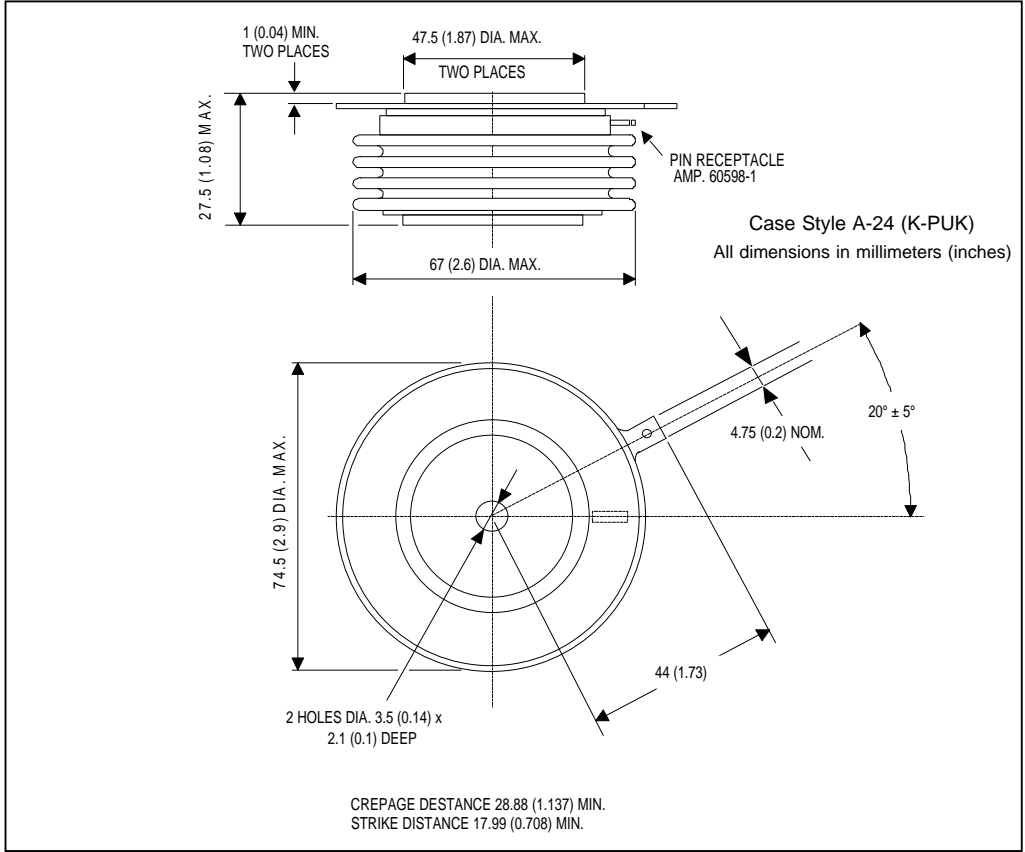


Fig. 1 - Current Ratings Characteristics

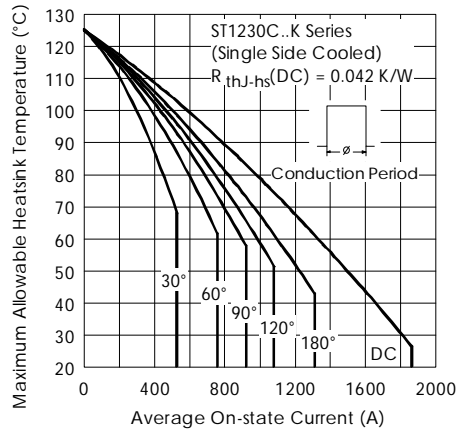


Fig. 2 - Current Ratings Characteristics

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

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В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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